



No.4753

2SK2260

N-Channel Silicon MOSFET

Very High-Speed
Switching Applications

Features

- Low ON resistance
- Very high-speed switching
- Low-voltage drive

Absolute Maximum Ratings at Ta = 25°C

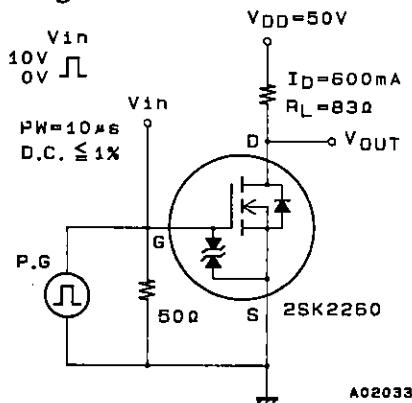
			unit
Drain-to-Source Voltage	V _{DSS}	150	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Drain Current(DC)	I _D	1.2	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	4.8 A
Allowable Power Dissipation	P _D	Tc = 25°C	3.5 W
		Mounted on ceramic board (250mm ² × 0.8mm)	1.5 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

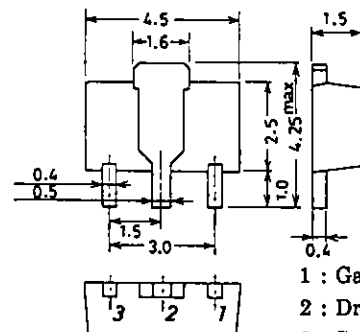
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	150			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = 150V, V _{GS} = 0			100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±18V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	1.5		2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10V, I _D = 600mA	0.8	1.1		S
Static Drain-to-Source On-state Resistance	R _{DS(on)}	I _D = 600mA, V _{GS} = 10V		1.6	2.2	Ω
Input Capacitance	C _{iss}	V _{DS} = 20V, f = 1MHz		80		pF
Output Capacitance	C _{oss}	V _{DS} = 20V, f = 1MHz		25		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 20V, f = 1MHz		8.5		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit		10		ns
Rise Time	t _r	"		15		ns
Turn-OFF Delay Time	t _{d(off)}	"		50		ns
Fall Time	t _f	"		30		ns
Diode Forward Voltage	V _{SD}	I _S = 1.2A, V _{GS} = 0		1.0		V

Marking : KO

Switching Time Test Circuit

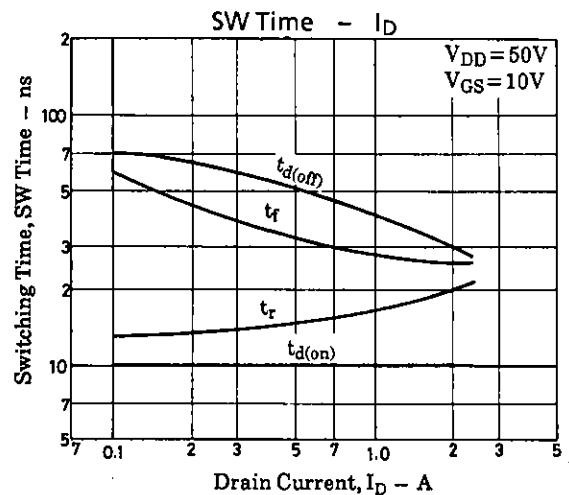
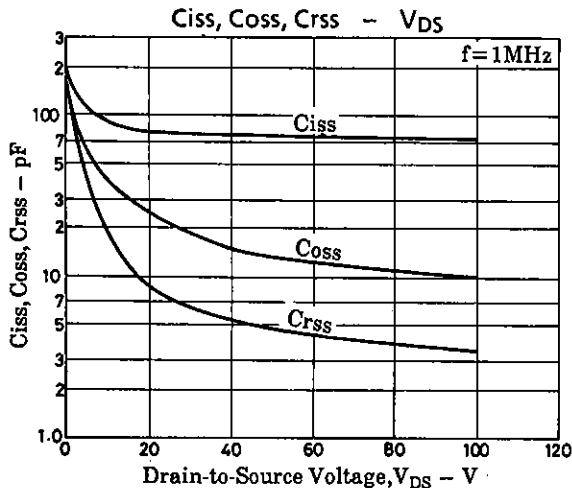
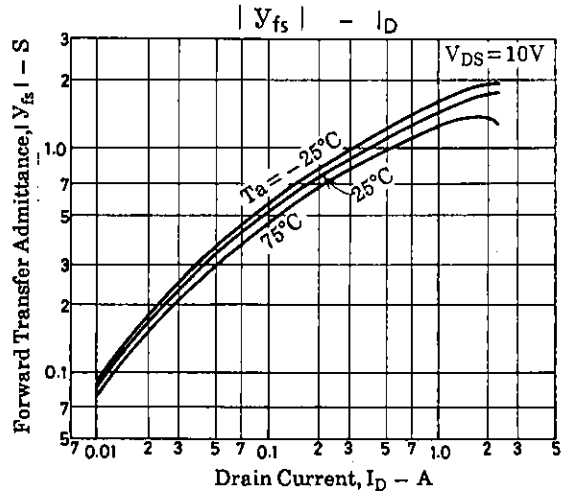
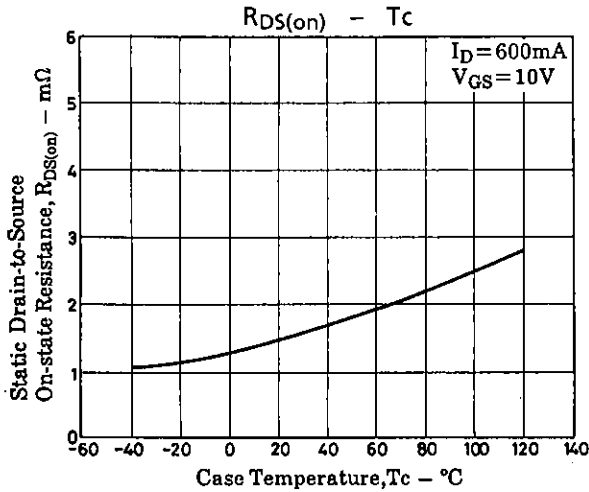
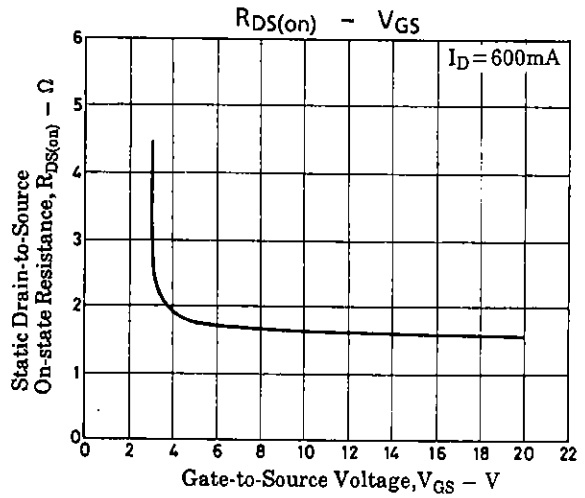
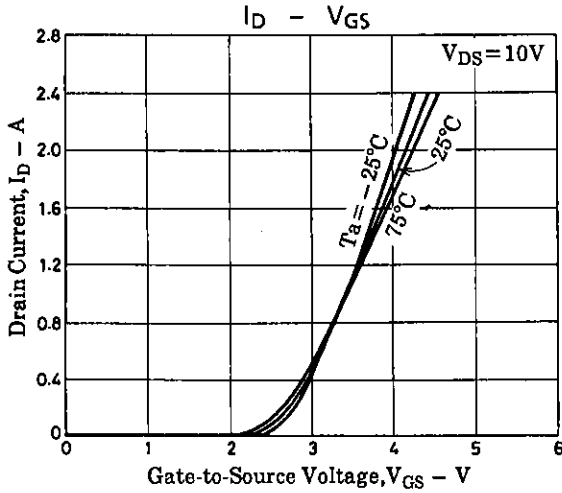
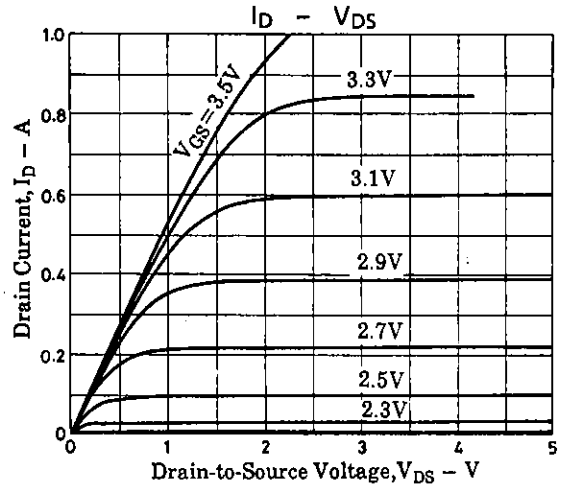
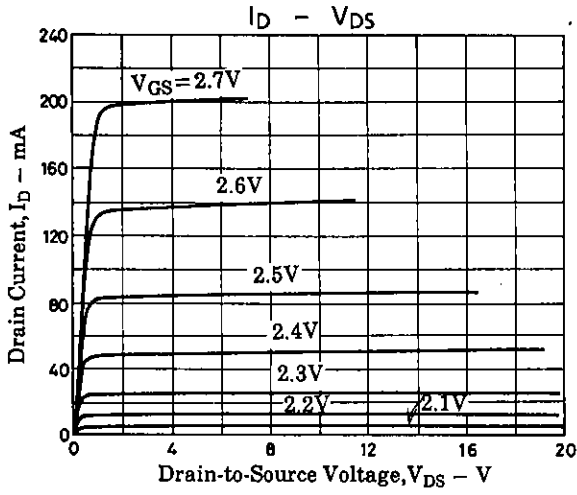


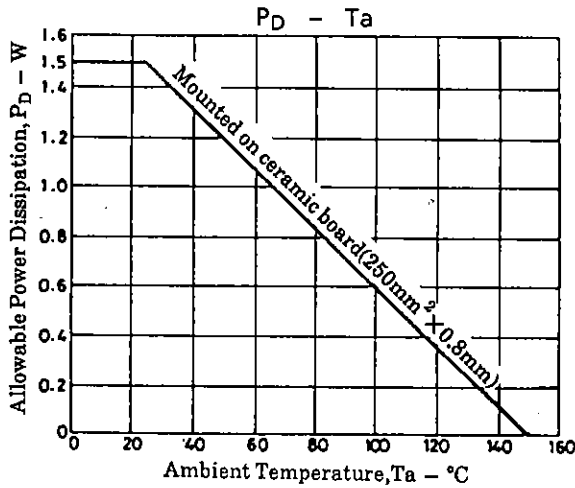
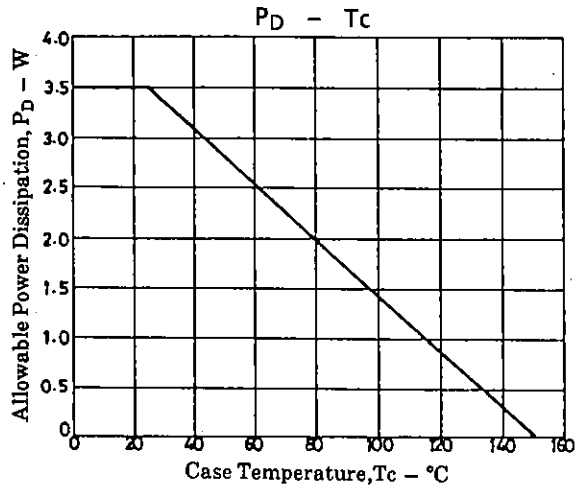
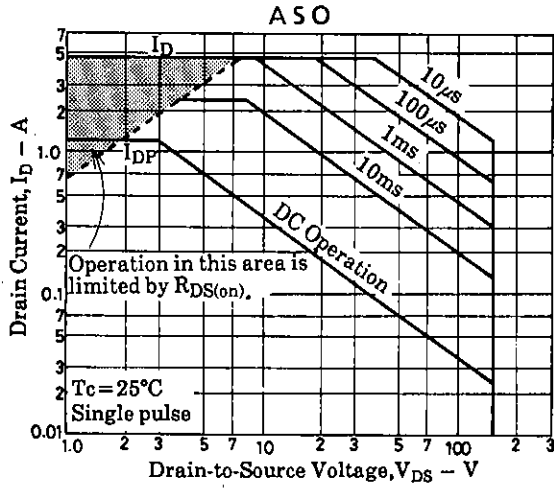
Package Dimensions 2062A
(unit : mm)



1 : Gate
2 : Drain
3 : Source
SANYO : PCP
(Bottom View)

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